



Docket No.: 21302/0203830-US0  
(PATENT)

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Patent Application of:  
Euijoon Yoon et al.

Application No.: 10/563,854

Confirmation No.: 3828

Filed: June 9, 2006

Art Unit: 2823

For: GROWTH METHOD FOR NITRIDE  
SEMICONDUCTOR EPITAXIAL LAYERS

Examiner: Maldonado, J. J.

**AMENDMENT ACCOMPANYING REQUEST FOR CONTINUED EXAMINATION**

MS RCE  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

March 8, 2008

Dear Sir:

**INTRODUCTORY COMMENTS**

This Amendment is submitted concurrently with a Request for Continued Examination (RCE) for the above-identified application.

In response to the Final Office Action dated December 8, 2009, and the mailing of an Advisory Action dated February 25, 2009, please amend the above-identified U.S. patent application as follows:

**Amendments to the Claims** are reflected in the listing of claims which begins on page 2 of this paper.

**Remarks/Arguments** begin on page 6 of this paper.